

SOT-523 Plastic-Encapsulate MOSFET

60V N-Channel MOSFET

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
60V	0.85Ω@10V	0.34A
	0.95Ω@4.5V	

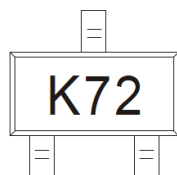
Feature

- Trench Technology Power MOSFET
- Low $R_{DS(ON)}$
- Low Gate Charge

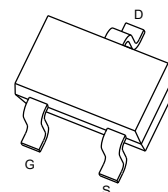
Application

- Load Switch
- DC/DC Converter

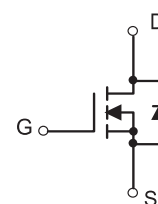
MARKING:



SOT-523



Schematic diagram



ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain - Source Voltage	V_{DS}	60	V
Gate - Source Voltage	V_{GS}	±20	V
Continuous Drain Current ^{1,5}	I_D	0.34	A
Pulsed Drain Current ²	I_{DM}	1.0	A
Power Dissipation ^{4,5}	P_D	0.25	W
Thermal Resistance from Junction to Ambient ⁵	$R_{\theta JA}$	500	°C/W
Junction Temperature	T_J	150	°C
Storage Temperature	T_{STG}	-55~ +150	°C

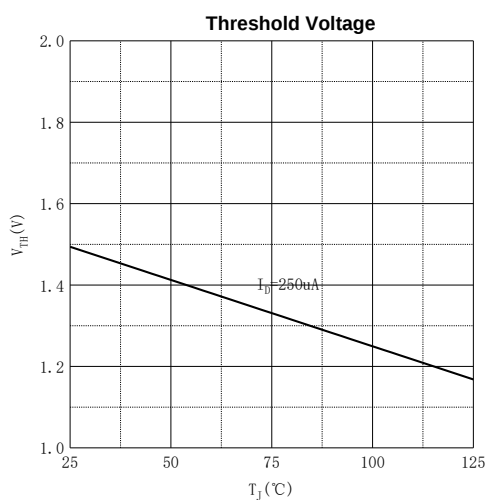
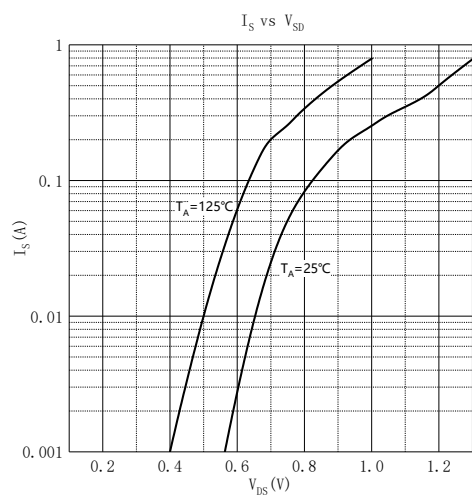
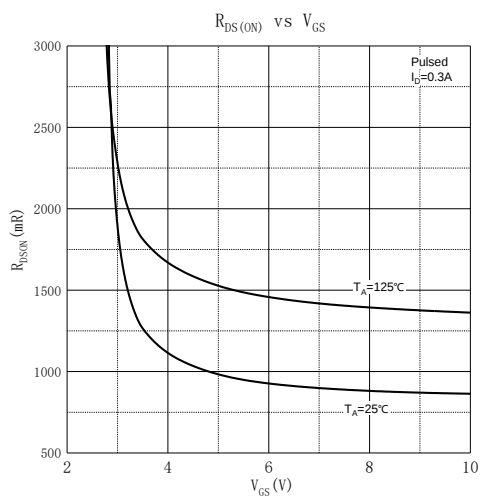
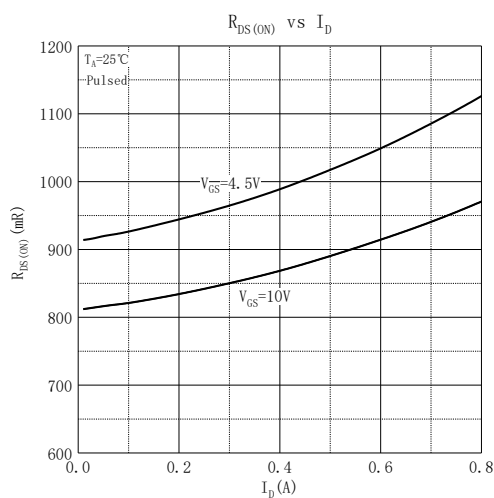
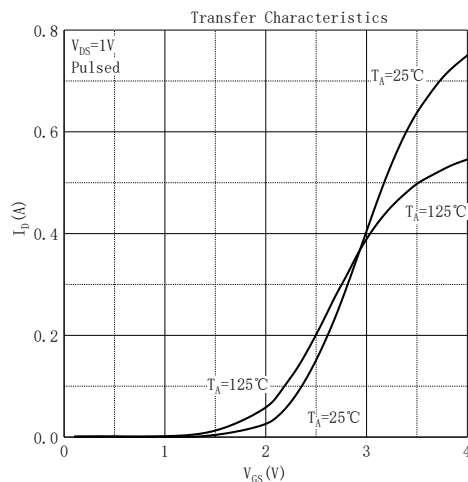
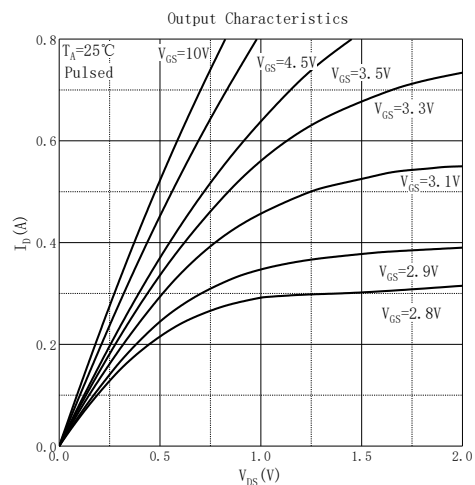
Electrical Characteristics ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Off Characteristics						
Drain - Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D = 250μA	60			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 48V, V _{GS} = 0V			1	μA
Gate - Body Leakage Current	I _{GSS}	V _{GS} = ±20V, V _{DS} = 0V			±95	nA
On Characteristics ³						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250μA	1	1.5	2.5	V
Drain-source On-resistance	R _{DS(on)}	V _{GS} = 10V, I _D = 0.3A		0.85	2.5	Ω
		V _{GS} = 4.5V, I _D = 0.2A		0.95	3	
Dynamic Characteristics						
Input Capacitance	C _{iss}	V _{DS} = 30V, V _{GS} = 0V, f = 1MHz		34.8		pF
Output Capacitance	C _{oss}			6.4		
Reverse Transfer Capacitance	C _{rss}			3.5		
Gate Resistance	R _g	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz		40		Ω
Switching Characteristics						
Total Gate Charge	Q _g	V _{DS} = 30V, V _{GS} = 10V, I _D = 0.3A		0.32		nC
Gate-source Charge	Q _{gs}			0.25		
Gate-drain Charge	Q _{gd}			0.17		
Turn-on Delay Time	t _{d(on)}	V _{DD} = 30V, V _{GS} = 10V, R _L = 100Ω, R _G = 3Ω		3.8		ns
Turn-on Rise Time	t _r			2.9		
Turn-off Delay Ttime	t _{d(off)}			14		
Turn-off Fall Time	t _f			8		
Source - Drain Diode Characteristics						
Diode Forward Voltage ³	V _{SD}	V _{GS} = 0V, I _S = 0.3A			1.2	V

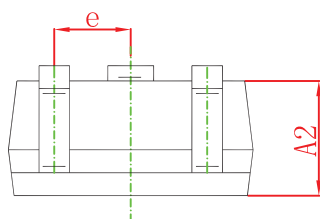
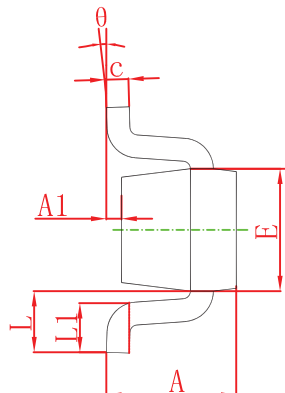
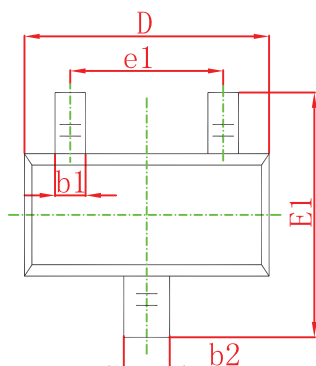
Notes :

- 1.The maximum current rating is limited by package.
- 2.Pulse Test : Pulse Width $\leq 10\mu s$, duty cycle $\leq 1\%$.
- 3.Pulse Test : Pulse Width $\leq 300\mu s$, duty cycle $\leq 2\%$.
- 4.The power dissipation P_D is limited by $T_{J(MAX)} = 150^{\circ}\text{C}$.
- 5.Device mounted on $1in^2$ FR-4 board with 2oz. Copper, in a still air environment with $T_A = 25^{\circ}\text{C}$.

Typical Characteristics



SOT-523 Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.700	0.900	0.028	0.035
A1	0.000	0.100	0.000	0.004
A2	0.700	0.800	0.028	0.031
b1	0.150	0.250	0.006	0.010
b2	0.250	0.350	0.010	0.014
c	0.100	0.200	0.004	0.008
D	1.500	1.700	0.059	0.067
E	0.700	0.900	0.028	0.035
E1	1.450	1.750	0.057	0.069
e	0.500 TYP.		0.020 TYP.	
e1	0.900	1.100	0.035	0.043
L	0.400 REF.		0.016 REF.	
L1	0.260	0.460	0.010	0.018
θ	0°	8°	0°	8°

NOTICE

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